PS3N0183P1

30V N-Channel MOSFETs

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max.	ID
30 V	12 mΩ @ 10 V	35 A
	18 mΩ @ 4.5 V	

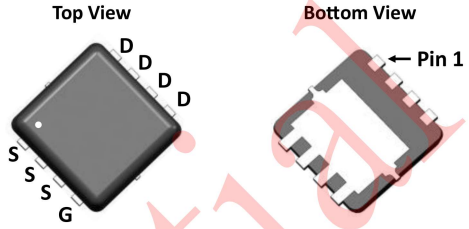
General Description

This device has been developed using Trench technology, these products have been designed to minimize on-state resistance and fast switching performance. These products are suited for high efficiency power management applications.

Features

- Low On-Resistance
- Low Gate Charge
- RoHS Compliant and Halogen Free

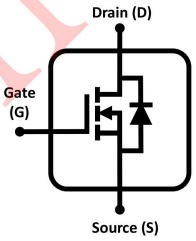
PPAK3x3-8L



Applications

- Load Switch
- Battery Charge/Discharge
- DC to DC Converters

Pin Configuration



Absolute Maximum Ratings (T_J=25°C, unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-Source Voltage		30	V
V_{GS}	Gate-Source Voltage		±20	
I_D	Drain Current-Continuous [A]	T_C=25 °C	35	A
		T_C=100 °C	22	
I_{DM}	Drain Current-Pulsed [A, B]	T_C=25°C	140	A
I_{AS}	Non-repetitive Avalanche Current [E]		16	A
E_{AS}	Single Pulse Drain-to-Source Avalanche Energy [E]		13	mJ
P_D	Maximum Power Dissipation	T_C=25 °C	27	W
		T_C=100 °C	10.9	
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C

Thermal Characteristics

Symbol	Parameter	Conditions	Value	Unit
$R_{\theta JA}$	Junction-to-Ambient [C]	Steady State	62	°C/W
$R_{\theta JC}$	Junction-to-Case	Steady State	4.6	°C/W